Abstrct

It is an object of the present invention to provide a highly reliable and high-quality semiconductor element by effectively preventing the migration of silver to a nitride semiconductor when an electrode main entirely or mostly of silver having high reflection efficiency is formed in contact with a nitride semiconductor layer. A semiconductor element comprises a nitride semiconductor layer, an electrode connected to said nitride semiconductor layer, and an insulating film covering at least part of said electrode, wherein the electrode comprises: a first metal film including silver or a silver alloy and in contact with the nitride semiconductor layer; and a second metal film completely covering the first metal film, and the insulating film comprises a nitride film.